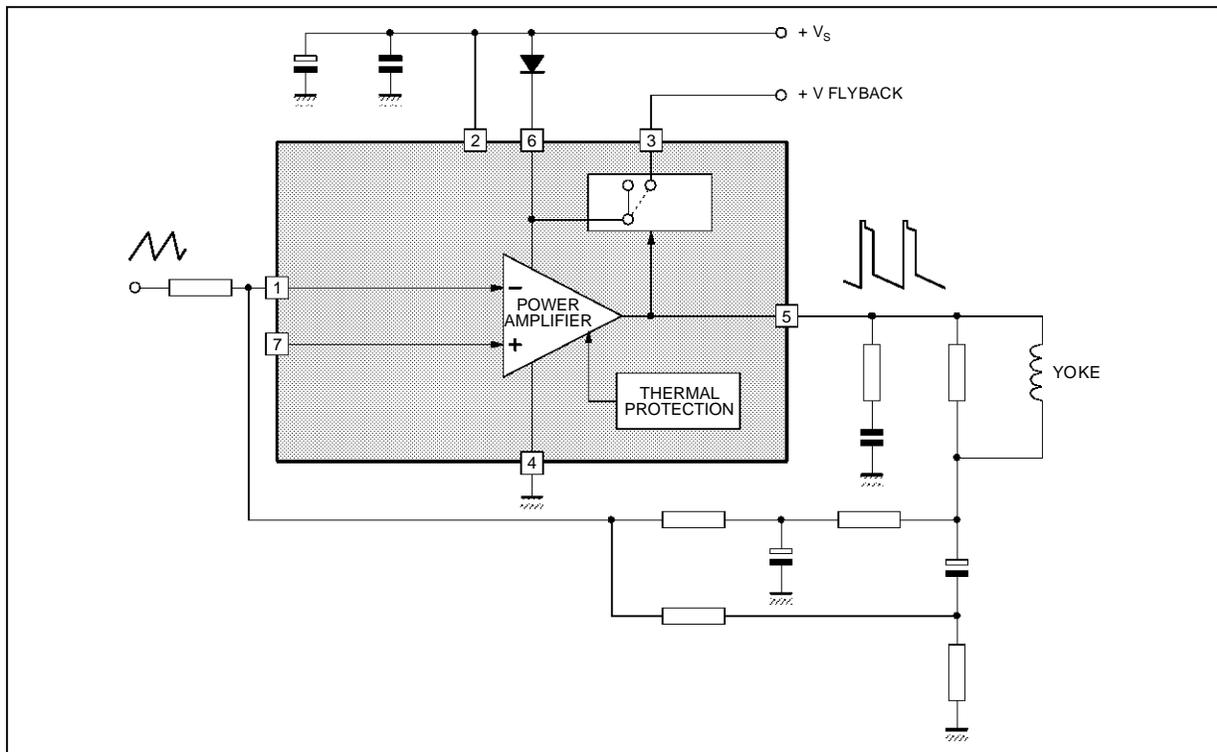




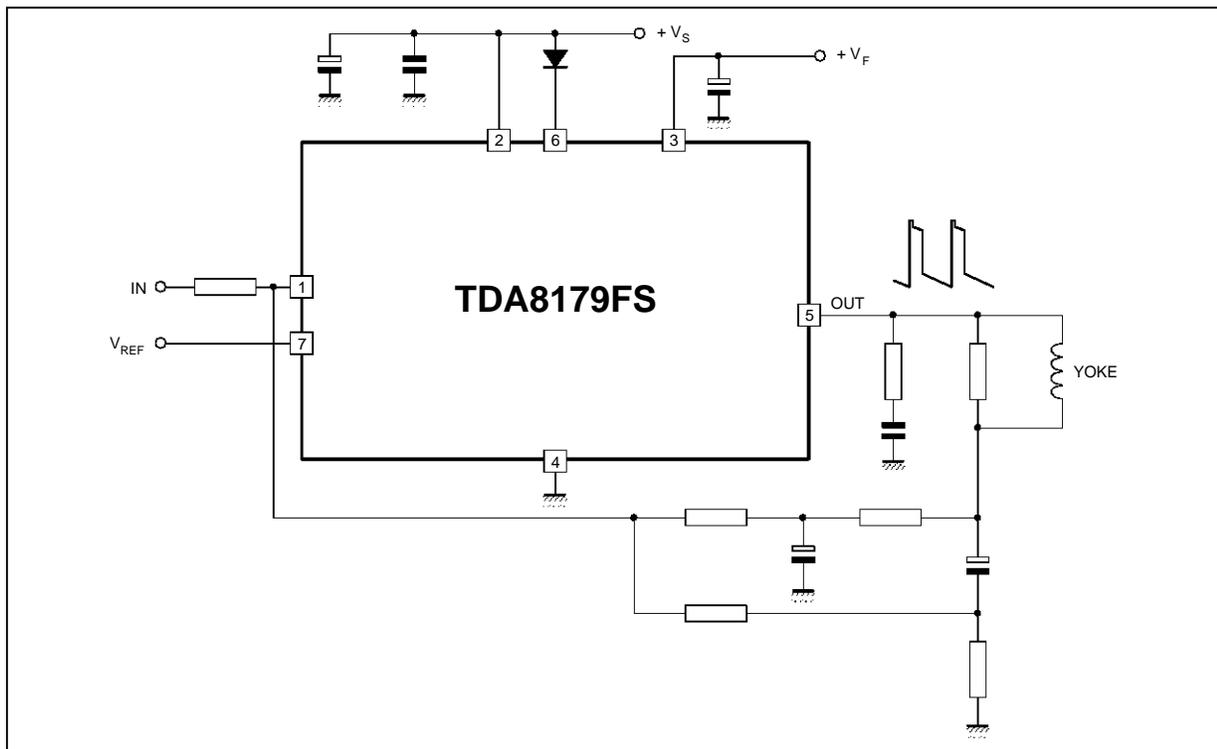
# TDA8179FS

## BLOCK DIAGRAM



8179F-02.EPS

## APPLICATION CIRCUIT



8179F-03.EPS

Note : For values see " Easy Design of Vertical Deflection Stages" (software available from our sales offices)

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>S</sub>	Supply Voltage (pin 2)	50	V
V <sub>F</sub>	Flyback Supply Voltage	100	V
V <sub>F</sub> - V <sub>S</sub>	Difference between Flyback Supply Voltage and Supply Voltage	50	V
V <sub>1</sub> , V <sub>7</sub>	Amplifier Input Voltage	+ V <sub>S</sub>	
I <sub>O</sub>	Output Peak Current	2 2 1.8	A
I <sub>3</sub>	Pin 3 Peak Flyback Current at f = 50 or 60Hz, t <sub>fly</sub> ≤ 1.5ms	1.8	A
P <sub>tot</sub>	Total Power Dissipation at T <sub>C</sub> = 70°C	20	W
T <sub>stg</sub>	Storage Temperature	- 40, + 150	°C
T <sub>j</sub>	Junction Temperature	0, +150	°C

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## THERMAL DATA

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction-case Thermal Resistance	Max. 3	°C/W

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## ELECTRICAL CHARACTERISTICS

(V<sub>7</sub> = 2.2V, V<sub>S</sub> = 42V, T<sub>A</sub> = 25°C, unless otherwise specified)

(refer to the test circuits - see Figure 1 next page)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>S</sub>	Operating Supply Voltage Range		10		42	V
I <sub>2</sub>	Pin 2 Quiescent Current	I <sub>3</sub> = 0 I <sub>5</sub> = 0		10	20	mA
I <sub>6</sub>	Pin 6 Quiescent Current	I <sub>3</sub> = 0 I <sub>5</sub> = 0		20	40	mA
I <sub>1</sub>	Amplifier Bias Current	V <sub>1</sub> = 1V		- 0.2	- 1	μA
V <sub>5</sub>	Quiescent Output Voltage	V <sub>S</sub> = 42V R <sub>a</sub> = 3.9kΩ V <sub>S</sub> = 35V R <sub>a</sub> = 5.6kΩ	23.4 17	24.2 17.8	25 18.5	V
V <sub>5L</sub>	Output Saturation Voltage to GND	I <sub>5</sub> = 1A		1.2	1.5	V
V <sub>5H</sub>	Output Saturation Voltage to Supply	- I <sub>5</sub> = 1A		2.2	2.6	V
V <sub>D5-6</sub>	Diode Forward Voltage between Pins 5-6	I <sub>D</sub> = 1A		1.5	3	V
V <sub>D3-6</sub>	Diode Forward Voltage between Pins 3-6	I <sub>D</sub> = 1A		1.5	3	V
R <sub>1</sub>	Input Resistance			200		kΩ
T <sub>j</sub>	Junction Temperature for Thermal Shutdown			140		°C

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FIGURE 1 : DC Test Circuits

Figure 1a : Measurement of  $I_1$ ,  $I_2$ ,  $I_6$

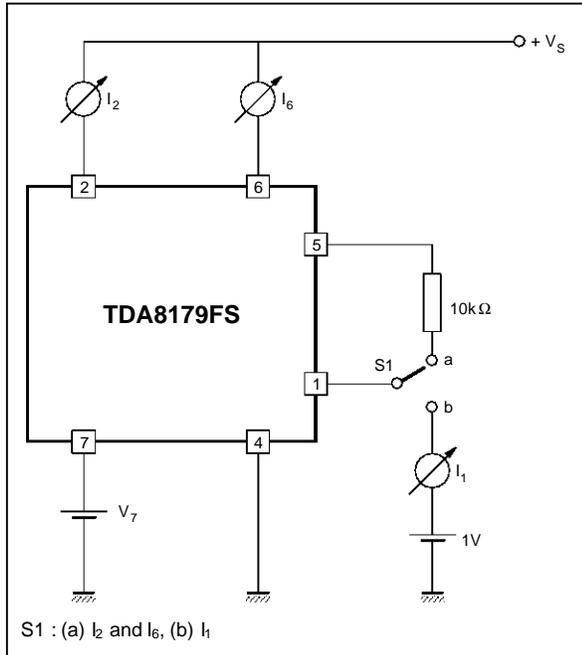


Figure 1b : Measurement of  $V_{5H}$

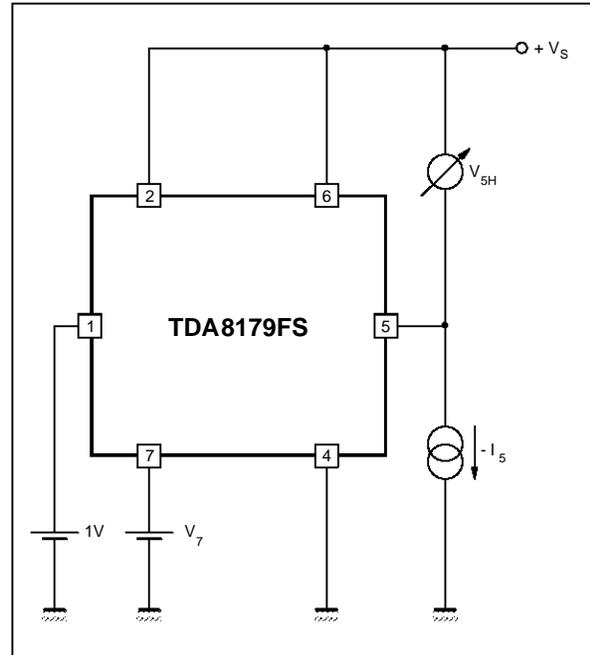


Figure 1c : Measurement of  $V_{5L}$

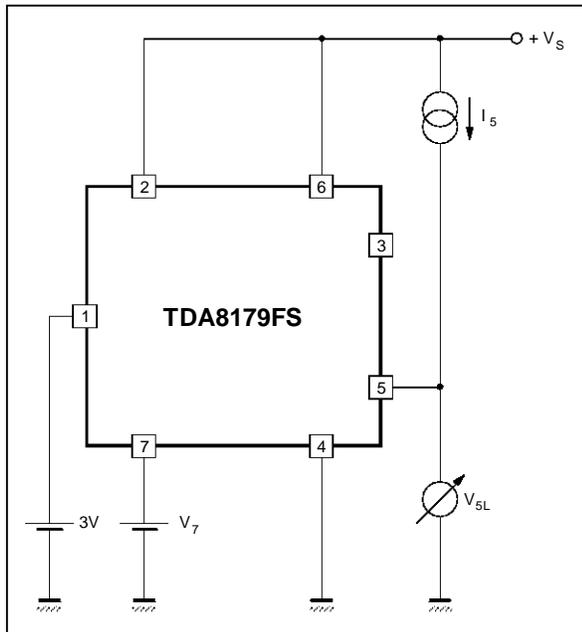


Figure 1d : Measurement of  $V_5$

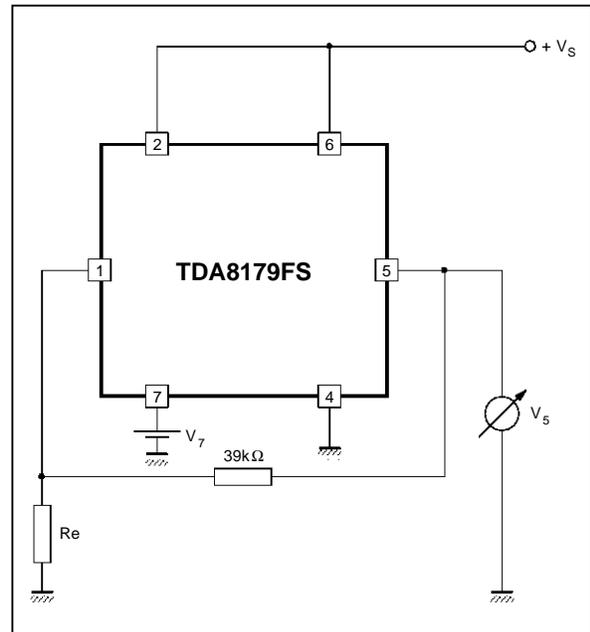
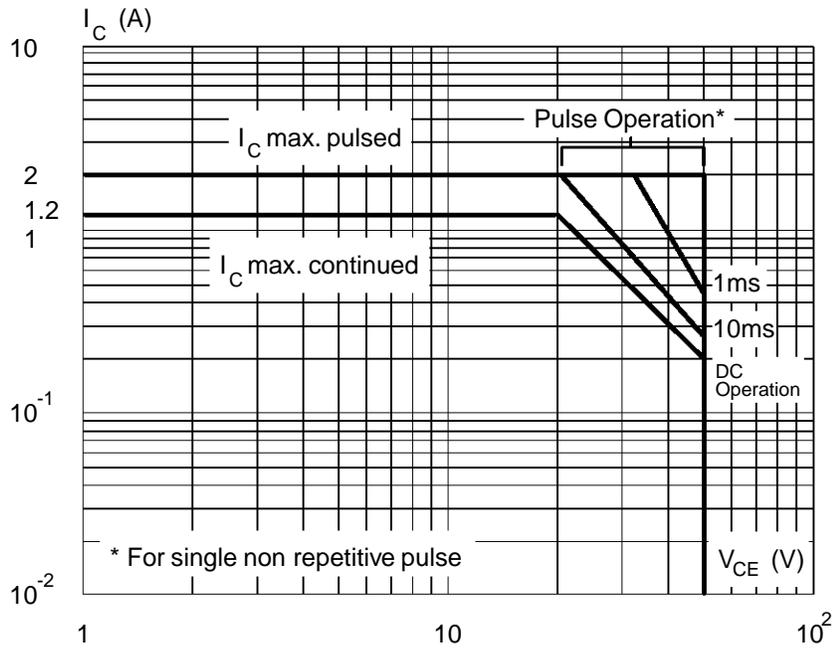
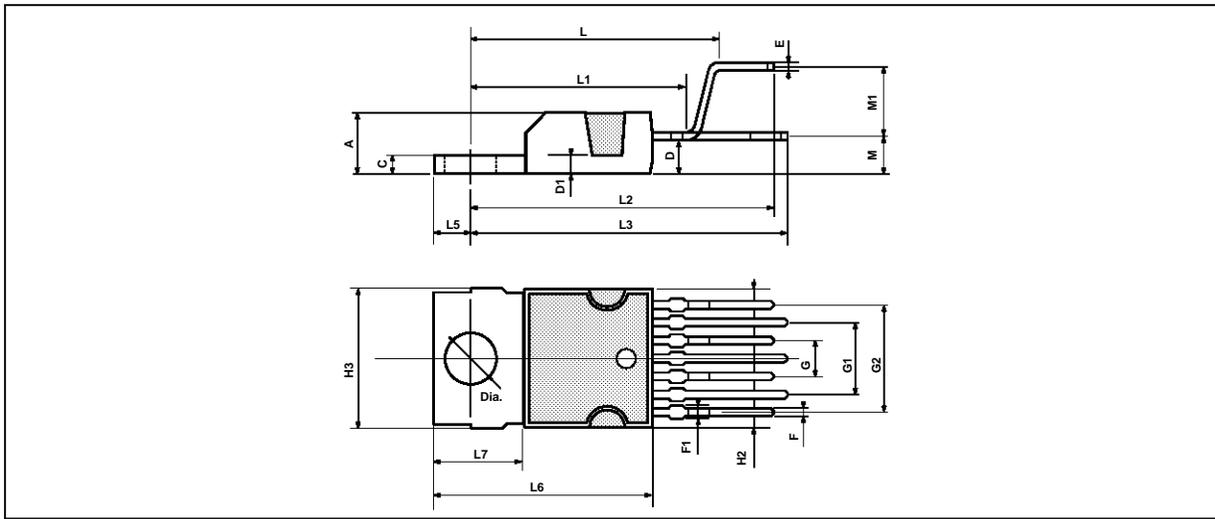


Figure 2 : SOA of Each Output Power Transistor at  $T_A = 25^\circ\text{C}$



8179F-08.EPS

PACKAGE MECHANICAL DATA : HEPTAWATT



PM-HEPTV/EP5

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		2.8			0.110	
M1		5.08			0.200	
Dia.	3.65		3.85	0.144		0.152

HEPTV/TBL

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